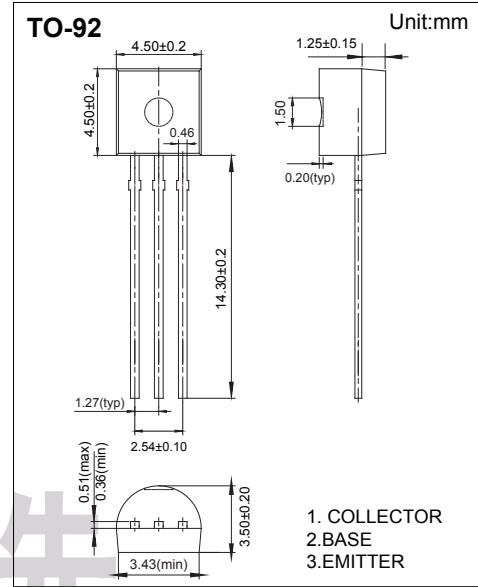


PNP Transistors BC556~BC558

■ Features

- High Voltage
- Complement to BC546,BC547,BC548



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	BC556	-80	V
	BC557	-50	
	BC558	-30	
Collector - Emitter Voltage	BC556	-64	
	BC557	-45	
	BC558	-30	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _c	-0.1	A
Collector Power Dissipation	P _c	625	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	200	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	

Transistor

PNP Transistors BC556~BC558

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Collecto- base breakdown voltage	BC556	Ic= -100 μA, IE=0	-80			V	
	BC557		-50				
	BC558		-30				
Collector- emitter breakdown voltage	BC556	Ic= -2 mA, IB=0	-65			V	
	BC557		-45				
	BC558		-30				
Emitter - base breakdown voltage	VEBO	IE= -100 μA, IC=0	-5				
Collector cut-off current	BC556	ICBO			-0.1	μA	
	BC557						VCB= -45 V, IE=0
	BC558						VCB= -25 V, IE=0
Collector cut-off current	BC556	ICEO			-0.1	μA	
	BC557						VCE= -60 V, IB=0
	BC558						VCE= -40 V, IB=0
Emitter cut-off current	IEBO	VEB= -5V, IC=0			-0.1		
Collector-emitter saturation voltage	VCE(sat)	IC=-10 mA, IB= -0.5mA			-0.3	V	
		IC=-100 mA, IB= -5mA			-0.65		
Base - emitter saturation voltage	VBE(sat)	IC=-10 mA, IB= -0.5mA			-0.8	V	
		IC=-100 mA, IB= -5mA			-1		
Base-emitter voltage	VBE	VCE=-5V, IC=-2mA	-0.55		-0.7		
		VCE=-5V, IC=-10mA			-0.82		
DC current gain	hFE	VCE= -5V, IC= -2mA	120		800		
Collector output capacitance	Cob	VCB=-10V,IE=0, f=1MHz			6	pF	
Transition frequency	fT	VCE= -5V, IC= -10mA,f=100MHz		150		MHz	

■ Classification of hFE

Rank	A	B	C
Range	120-220	180-460	420-800